

Class A, Class AB Microwave Power Silicon NPN Transistor 0.7 W, 960–1215 MHz, 18V

Features

- Guaranteed performance @ 1090 MHz, 18 Vdc Class A
- Output power: 0.2W
- Minimum gain: 10dB
- 100% tested for load mismatch at all phase angles with 10:1 VSWR
- Industry standard package
- Nitride passivated
- Gold metallized, emitter ballasted for long life and resistance to metal migration
- Internal input matching for broadband operation

Description and Applications

Designed for Class A and AB common emitter amplifier applications in the low–power stages of IFF, DME, TACAN, radar transmitters, and CW systems.

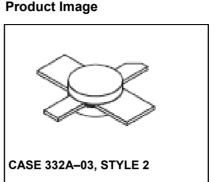
MAXIMUM RATINGS

Rating	Symbol	Value		Unit			
Collector–Emitter Voltage	V _{CEO}	20		Vdc			
Collector-Base Voltage	V _{CBO}	5	0	Vdc			
Emitter–Base Voltage	V _{EBO}	3.5		Vdc			
Collector Current — Continuous	lc	200		mAdc			
Total Device Dissipation @ T _C = 25°C (1) Derate above 25°C	PD	7.0 40		Watts mW/∘C			
THERMAL CHARACTERISTICS	I	I		I			
Characteristic	Characteristic		nbol	Max		Unit	
Thermal Resistance, Junction to Case (2)		Re	R _{eJC}			°C/W	
ELECTRICAL CHARACTERISTICS ($T_c = 25^{\circ}C$ unless	ss otherwise not	ted.)					
Characteristic	9	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector–Emitter Breakdown Voltage (I _C = 5.0 mAdc, I _B = 0)	V	(BR)CEO	20	-	-	Vdc	
Collector–Emitter Breakdown Voltage (I _C = 5.0 mAdc, V _{BE} = 0)	V	V _{(BR)CES} 5		-	-	Vdc	
Collector–Base Breakdown Voltage (I _C = 5.0 mAdc, I _E = 0)	V	V _{(BR)CBO} 50		-	-	Vdc	
Emitter–Base Breakdown Voltage (I _E = 1.0 mAdc, I _C = 0)	V	V _{(BR)EBO} 3		-	-	Vdc	
Collector Cutoff Current (V _{CB} = 20 Vdc, I _E = 0)		I _{CBO} —		-	0.5	mAdc	
ON CHARACTERISTICS							
DC Current Gain (I _C = 100 mAdc, V _{CE} = 5.0 Vdc)		h _{FE}	10	—	100	-	

1. These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers. 2. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

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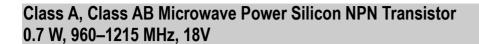
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Characteristic	Symbol	Min	Тур	Max	Unit	
	Symbol		-96	IIIda	onic	
Output Capacitance (V _{CB} = 28 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	-	2.0	5.0	pF	
UNCTIONAL TESTS	-	1	1	1	1	
Common–Emitter Power Gain — Class A (V _{CE} = 18 Vdc, I _C = 100 mAdc, f = 1090 MHz, P _{out} = 200 mW)	G _{PE}	10	12	-	dB	
Common–Emitter Power Gain — Class AB (V _{CE} = 18 Vdc, I _{CQ} = 10 mAdc, f = 1090 MHz, P _{out} = 0.7 W)	G _{PE}	-	10.7	-	dB	
Load Mismatch — Class A (V _{CE} = 18 Vdc, I _C = 100 mAdc, f = 1090 MHz, P _{out} = 200 mW, VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Power Output				
1, C2, C3, C7, C8, C10 — 220 pF ATC 100 mil 4, C9 — 4.7 μ F 50 V Tantalum 5, C6 — 0.8–8.0 pF Johanson #7290 1–Z10 — Distributed Microstrip Elements — See Figure 8 bard Material — 0.031" Thick Teflon–Fiberglass $\varepsilon_r = 2.56$ RF INPUT $C1$ Z1 Z1 Z4 Z1 Z4 Z4 Z1 Z4 Z1 Z4 Z4 Z1 Z4 Z1 Z4 Z1 Z1 Z4 Z1						
Class AB Bias Control Circuit 18 V Output I _{CQ} 10 mA Nominal	Class A		urrent Bias mA, V _{CE} = 1	Control Circ 18 V	cuit	
$\begin{array}{c} 10 \ \mu\text{F} \\ 10 \ \mu\text{F} \\ 50 \ V \\ \hline 10 \ 1/2 \ W \ 1/2 \ W \ 1/2 \ U \$	R2 11 k 1/2 W 2N35 R5 18 k 1/2 W C4 50	R3 ≥ 1/2 W	$\begin{array}{c} C1 \underbrace{\downarrow} 10 \ \mu\text{F} \\ \underline{\downarrow} 50 \ V \\ C2 \underbrace{\downarrow} 50 \ V \\ \underline{\downarrow} 50 \ V \\ C3 \underbrace{\downarrow} 50 \ V \\ \underline{C3} \underbrace{\downarrow} 50 \ V \end{array}$	D +28 V INPUT D +18 V COLLEC OUTPUT TO P D BASE BIAS OL TO POINT B	OINT C	



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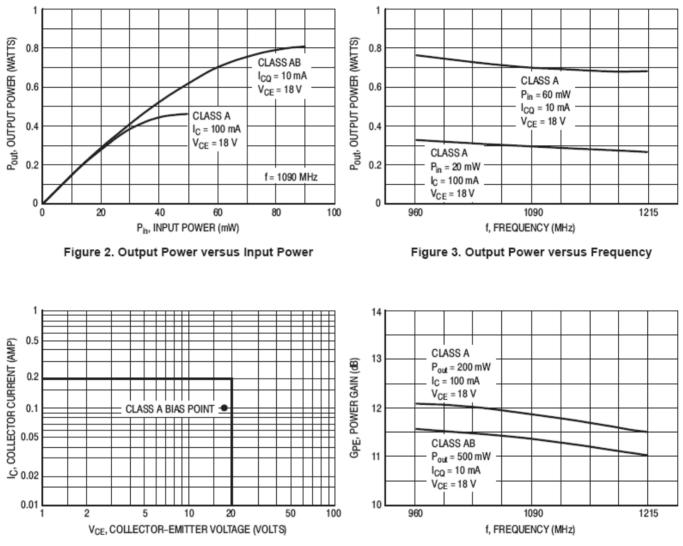


Figure 4. DC Safe Operating Area

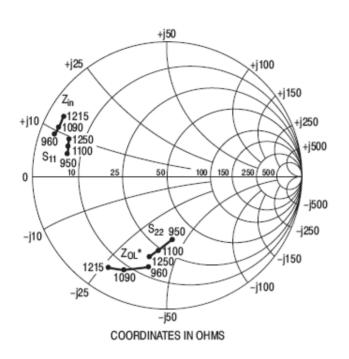
Figure 5. Power Gain versus Frequency

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SERIES EQUIVALENT IMPEDANCES $P_{out} = 0.5 \text{ W}, V_{CE} = 18 \text{ Vdc},$ $I_{CO} = 10 \text{ mAdc}, \text{ Class AB}$

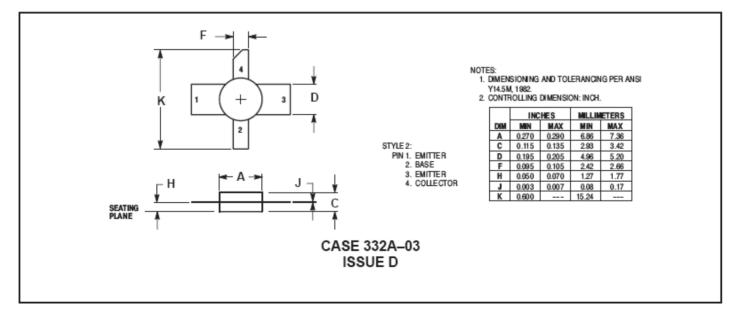
f Z _{in} MHz Ohms		Z _{OL} * Ohms		
960 1090 1215	3.0 + j9.0 3.2 + j10 2.8 + j12	16 – j40 8.5 – j31 7.0 – j26		

Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage, and frequency.

S-PARAMETERS - V_{CE} = 18 Vdc, I_C = 100 mAdc, Class A

F	\$ ₁₁		\$ ₂₁		\$ ₁₂		\$ ₂₂	
(MHz)	S ₁₁	∠¢	S ₂₁	∠¢	S ₁₂	∠¢	S ₂₂	∠¢
950	0.77	166	2.42	40	0.016	42	0.48	-87
1000	0.78	165	2.36	38	0.016	48	0.50	-90
1050	0.77	163	2.31	33	0.016	46	0.51	-94
1100	0.77	162	2.31	28	0.016	46	0.54	-97
1150	0.78	161	2.20	23	0.015	46	0.57	-100
1200	0.78	159	2.20	19	0.016	47	0.59	-103
1250	0.78	158	2.12	12	0.016	42	0.61	-106

Figure 6. Common–Emitter S–Parameters and Series Equivalent Input/Output Impedances Replaces MRF1000MA/D



PACKAGE DIMENSIONS

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